

Shubhra S Pasayat

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/5923287/publications.pdf>

Version: 2024-02-01

18
papers

403
citations

932766

10
h-index

887659

17
g-index

18
all docs

18
docs citations

18
times ranked

246
citing authors

#	ARTICLE	IF	CITATIONS
1	Demonstration of device-quality 60% relaxed In _{0.2} Ga _{0.8} N on porous GaN pseudo-substrates grown by PAMBE. Journal of Applied Physics, 2022, 131, .	1.1	7
2	Fully Relaxed, Crack-Free AlGa _N with upto 50% Al Composition Grown on Porous GaN Pseudo-Substrate. Crystals, 2022, 12, 989.	1.0	1
3	Metal Organic Vapor Phase Epitaxy of Thick N-Polar InGa _N Films. Electronics (Switzerland), 2021, 10, 1182.	1.8	3
4	Investigation and optimization of N-polar Ga _N porosification for regrowth of smooth hillocks-free Ga _N films. Applied Physics Letters, 2021, 119, .	1.5	2
5	Patterned III-Nitrides on Porous Ga _N : Extending Elastic Relaxation from the Nano to the Micrometer Scale. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2100234.	1.2	9
6	Demonstration of ultra-small ($\leq 10^{-4}$m) 632 nm red InGa _N micro-LEDs with useful on-wafer external quantum efficiency (>0.2%) for mini-displays. Applied Physics Express, 2021, 14, 011004.	1.1	96
7	Record-Low Thermal Boundary Resistance between Diamond and Ga _N -on-SiC for Enabling Radiofrequency Device Cooling. ACS Applied Materials & Interfaces, 2021, 13, 60553-60560.	4.0	42
8	Optimization of Digital Growth of Thick N-Polar InGa _N by MOCVD. Journal of Electronic Materials, 2020, 49, 3450-3454.	1.0	2
9	A Novel Concept using Derivative Superposition at the Device-Level to Reduce Linearity Sensitivity to Bias in N-polar Ga _N MISHEMT. , 2020, , .		5
10	Color-tunable $\leq 10^{-4}$m square InGa _N micro-LEDs on compliant Ga _N -on-porous-GaN pseudo-substrates. Applied Physics Letters, 2020, 117, .	1.5	44
11	Method of growing elastically relaxed crack-free AlGa _N on Ga _N as substrates for ultra-wide bandgap devices using porous Ga _N . Applied Physics Letters, 2020, 117, .	1.5	15
12	Growth of strain-relaxed InGa _N on micrometer-sized patterned compliant Ga _N pseudo-substrates. Applied Physics Letters, 2020, 116, .	1.5	38
13	High Linearity and High Gain Performance of N-Polar Ga _N MIS-HEMT at 30 GHz. IEEE Electron Device Letters, 2020, 41, 681-684.	2.2	46
14	First experimental demonstration and analysis of electrical transport characteristics of a Ga _N -based HEMT with a relaxed InGa _N channel. Semiconductor Science and Technology, 2020, 35, 075007.	1.0	9
15	Compliant Micron-Sized Patterned InGa _N Pseudo-Substrates Utilizing Porous Ga _N . Materials, 2020, 13, 213.	1.3	22
16	Fabrication of relaxed InGa _N pseudo-substrates composed of micron-sized pattern arrays with high fill factors using porous Ga _N . Semiconductor Science and Technology, 2019, 34, 115020.	1.0	30
17	First demonstration of improvement in hole conductivity in <i>c</i> -plane III-Nitrides through application of uniaxial strain. Japanese Journal of Applied Physics, 2019, 58, 030908.	0.8	16
18	First demonstration of RF N-polar Ga _N MIS-HEMTs grown on bulk Ga _N using PAMBE. Semiconductor Science and Technology, 2019, 34, 045009.	1.0	16